

Form 1449*	Atty. Docket No.: 303.684US3	Serial No. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	
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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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*Substitute Disclosure Statement Form (PTO-1449)

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Form 1449*	Atty. Docket No.: 303.684US3	Serial No. Unknown 10/043/065
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